• General Description

The ZM098N06I combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

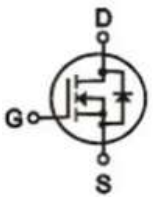
• Features

- ■ Advance high cell density Trench technology
- ■Low $R_{DS(ON)}$ to minimize conductive loss
- ■Low Gate Charge for fast switching
- ■Low Thermal resistance

•Application

- ■MB/VGA Vcore
- ■SMPS 2nd Synchronous Rectifier
- ■POL application
- ■BLDC Motor driver

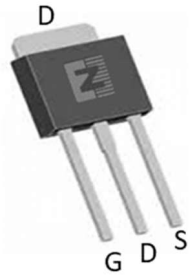
• Product Summary



V_{DS} =65V

$R_{DS(ON)}$ =11mΩ

I_D =50A



TO-251

•Ordering Information:

Part NO.	ZM098N06I
Marking	ZM098N06
Packing Information	TUBE BULK
Basic ordering unit (pcs)	3600

•Absolute Maximum Ratings (T_C =25℃)

Parameter	**Symbol**	Rating	Unit
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	$I_{D@}$TC=25℃	50	A
	$I_{D@}$TC=75℃	35	A
	$I_{D@}$TC=100℃	31.5	A
Pulsed Drain Current ①	I_{DM}	104	A
Total Power Dissipation(TC=25℃)	P_D@TC=25℃	70	W
Total Power Dissipation(TA=25℃)	P_D@TA=25℃	2.8	W
Operating Junction Temperature	T_J	-55 to 150	℃
Storage Temperature	T_{STG}	-55 to 150	℃
Single Pulse Avalanche Energy@L=0.1mH	E_{AS}	280	mJ
Avalanche Current@L=0.1mH	I_{AS}	75	A

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1.8	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	45	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V,I_D =250uA	65			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =250uA	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=60V, V_{GS} =0V			1.0	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V ,V_{DS} =0V			±100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=24A		11	13	mΩ
		V_{GS}=4.5V, I_D=12A		14	17	mΩ
Forward Transconductance	g_{FS}	V_{DS} =25V, I_D=10A		30		S
Source-drain voltage	V_{SD}	Is=24A			1.28	V

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	VDS=25V f = 1MHz	-	3220	-	pF
Output capacitance	C_{oss}		-	149	-	
Reverse transfer capacitance	C_{rss}		-	106	-	

●Gate Charge characteristics(Ta= 25℃)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	V_{DD} =15V I_D = 24A V_{GS} = 10V	-	30	-	nC
Gate - Source charge	Q_{gs}		-	9	-	
Gate - Drain charge	Q_{gd}		-	15	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

Fig.1 Power Dissipation

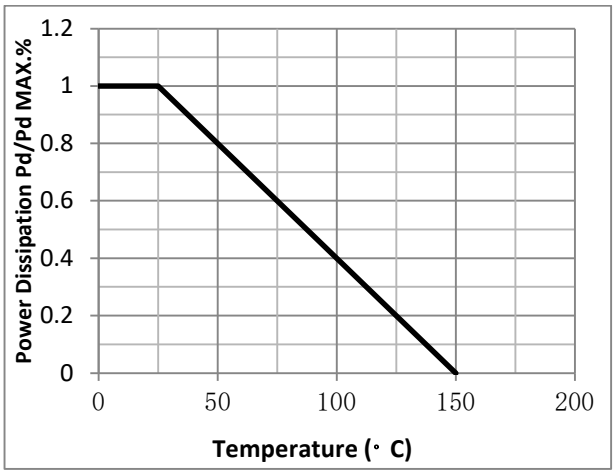


Fig.2 Typical output Characteristics

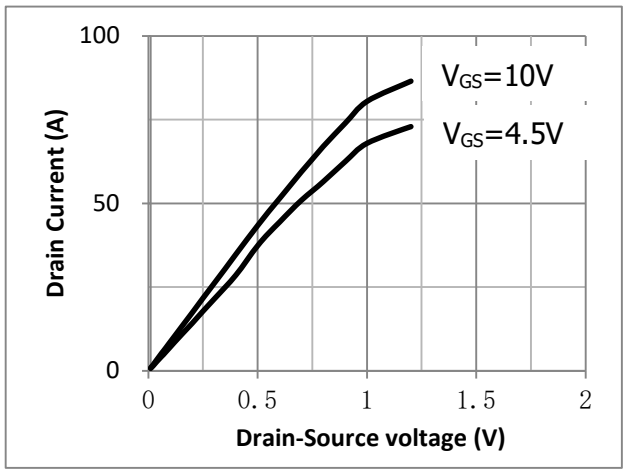


Fig.3 Threshold Voltage V.S Junction Temperature

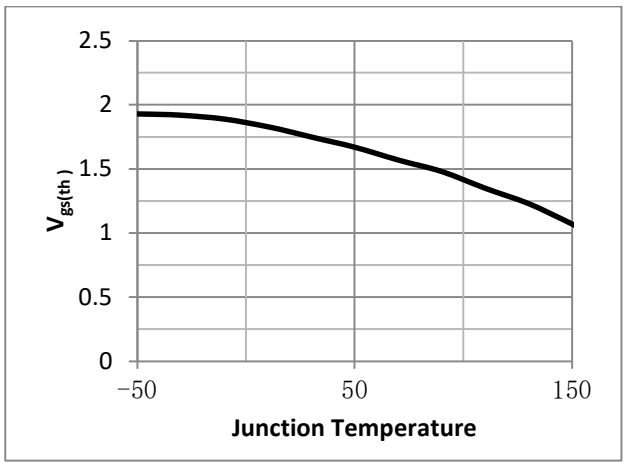


Fig.4 Resistance V.S Drain Current

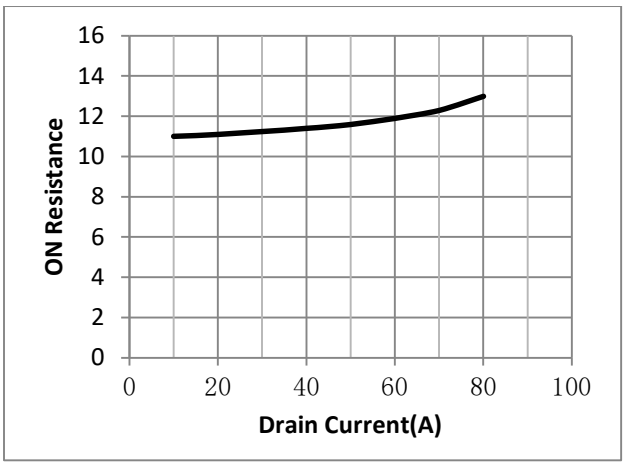


Fig.5 On-Resistance VS Gate Source Voltage

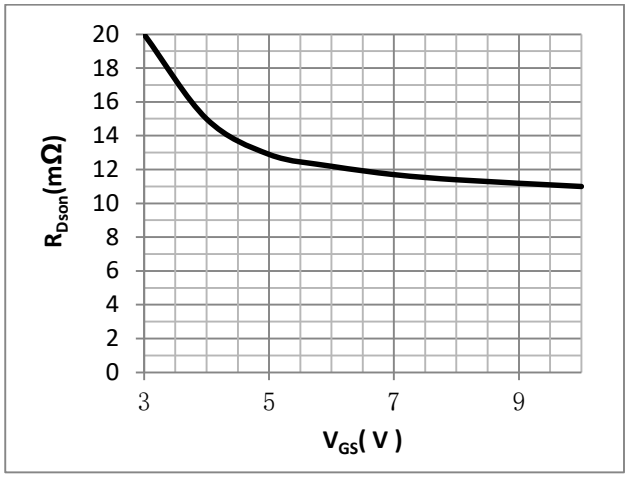


Fig.6 On-Resistance V.S Junction Temperature

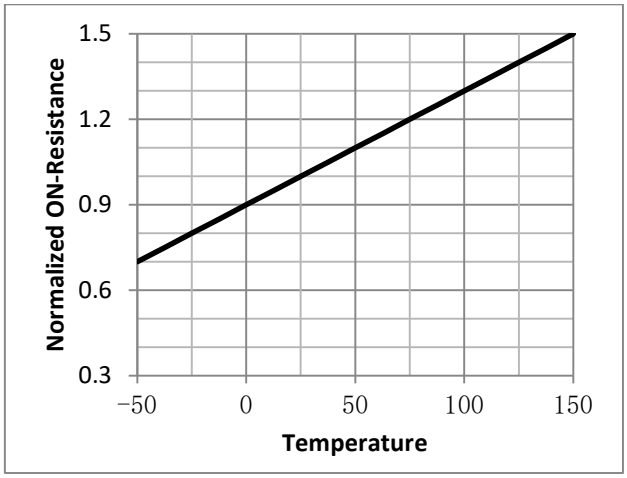


Fig.7 Gate Charge Measurement Circuit

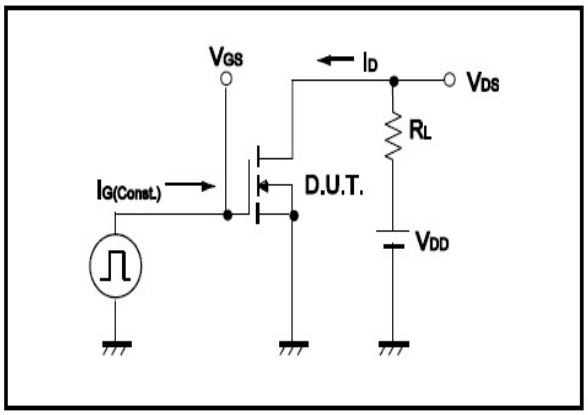


Fig.8 Gate Charge Waveform

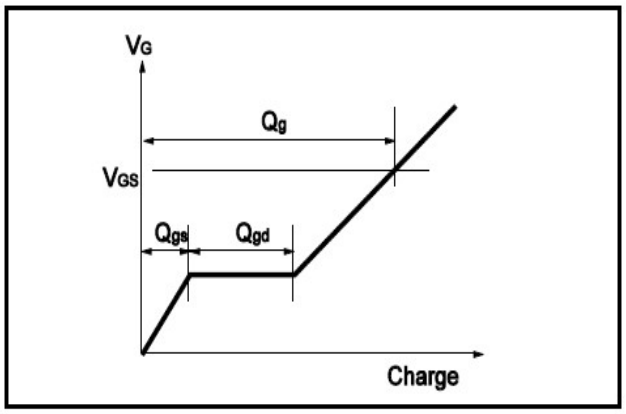


Fig.9 Switching Time Measurement Circuit

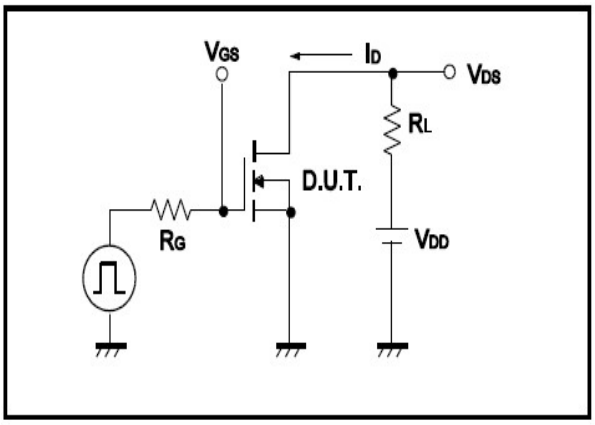


Fig.10 Switching Time Waveform

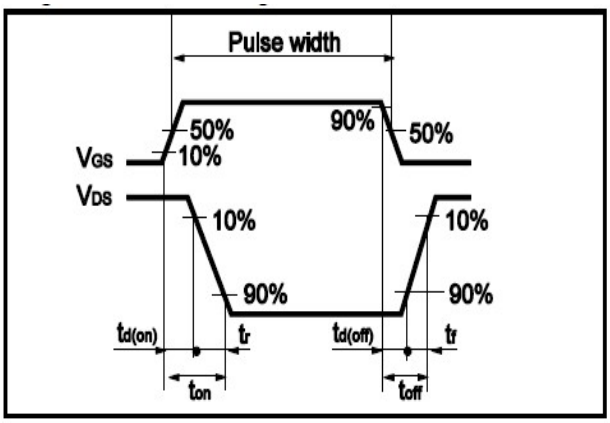


Fig.11 Avalanche Measurement Circuit

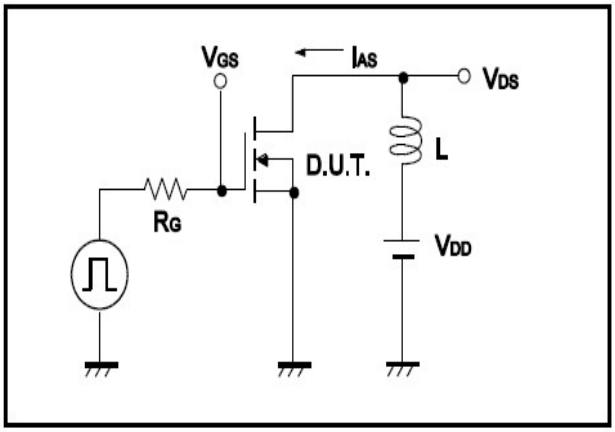
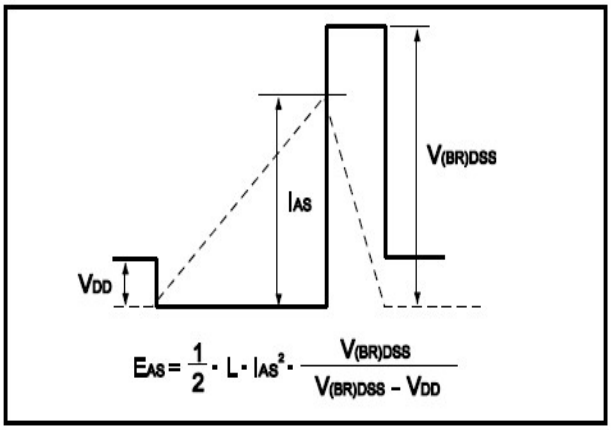


Fig.12 Avalanche Waveform



●Dimensions(TO-251)

Unit：mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	D	6.35	6.80
A1	0.95	1.30	D1	5.10	5.50
B	0.80	1.25	E	5.30	6.30
b	0.50	0.80	e	2.30	2.35
b1	0.70	0.90	L	7.00	9.20
c	0.45	0.70			
c1	0.45	0.70